

## ZXTP2029F 100V, SOT23, PNP medium power transistor

### Summary

 $V_{(BR)CEV}$  > -130V,  $V_{(BR)CEO}$  > -100V

 $I_{C(cont)} = -3A$ 

 $R_{CE(sat)} = 45m\Omega \text{ typical}$ 

V<sub>CE(sat)</sub> < -80mV @ -1A

 $P_{D} = 1.2W$ 

Complementary part number ZXTN2020F

## Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

## Features

- Higher power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 130V forward blocking voltage

### Applications

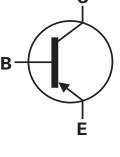
- MOSFET and IGBT gate driving
- Motor drive
- DC-DC converters
- High side switches

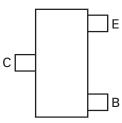
### **Ordering information**

Device	Reel size (inches)	Tape width	Quantity per reel
ZXTP2029FTA	7	8mm	3,000

### **Device marking**

953





Pinout - top view

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V <sub>CBO</sub>	-130	V
Collector-emitter voltage	V <sub>(BR)CEV</sub>	-130	V
Collector-emitter voltage	V <sub>CEO</sub>	-100	V
Emitter-base voltage	V <sub>EBO</sub>	-7.0	V
Peak pulse current	I <sub>СМ</sub>	-5	А
Continuous collector current <sup>(a)</sup>	Ι <sub>C</sub>	-3	А
Base current	Ι <sub>Β</sub>	-1	А
Power dissipation @ T <sub>A</sub> =25 <sup>o</sup> C <sup>(a)</sup> Linear derating factor	P <sub>D</sub>	1.0 8.0	W mW/ <sup>o</sup> C
Power dissipation @ T <sub>A</sub> =25 <sup>o</sup> C <sup>(b)</sup> Linear derating factor	P <sub>D</sub>	1.2 9.6	W mW/ <sup>o</sup> C
Power dissipation @ T <sub>A</sub> =25 <sup>o</sup> C <sup>(c)</sup> Linear derating factor	P <sub>D</sub>	1.56 12.5	W mW/ <sup>o</sup> C
Operating and storage temperature	T <sub>j</sub> :T <sub>stg</sub>	-55 to +150	°C

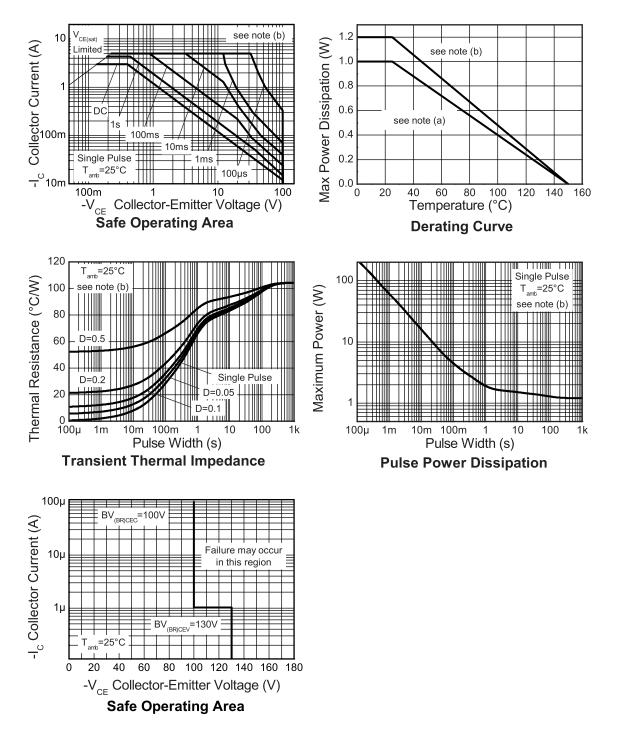
### **Thermal resistance**

Parameter	Symbol	Value	Unit
Junction to ambient <sup>(a)</sup>	$R\theta_{JA}$	125	°C/W
Junction to ambient <sup>(b)</sup>	$R\theta_{JA}$	104	°C/W
Junction to ambient <sup>(c)</sup>	$R\theta_{JA}$	80	°C/W

NOTES:

(a) Mounted on 18mm x 18mm x 1.6mm FR4 PCB with a very high coverage of 2 oz weight copper in still air conditions. (b) Mounted on 30mm x 30mm x 1.6mm FR4 PCB with a very high coverage of 2 oz weight copper in still air conditions. (c) As (b) above measured at t<5secs.

### **Characteristics**



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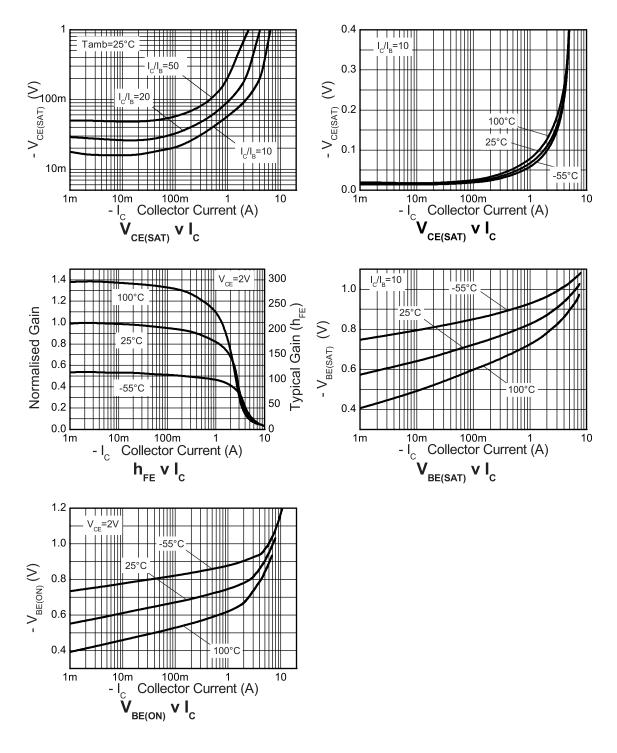
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	-130	-160		V	I <sub>C</sub> =-100μA
Collector-emitter breakdown voltage	V <sub>(BR)CEV</sub>	-130	-160		V	I <sub>C</sub> =–1μΑ, 1V> V <sub>BE</sub> >-0.3V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	-100	-120		V	I <sub>C</sub> =-10mA <sup>(a)</sup>
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	-7.0	-8.3		V	I <sub>E</sub> =-100μΑ
Collector-emitter cut-off current	I <sub>CEV</sub>			-20	nA	V <sub>CE</sub> =-100V, V <sub>BE</sub> = 1V
Collector-base cut-off current	I <sub>CBO</sub>			-20	nA	V <sub>CB</sub> =-100V
Emitter-base cut-off current	I <sub>EBO</sub>			-10	nA	V <sub>EB</sub> =-6V
Static forward current transfer ratio	H <sub>FE</sub>	100 100 40	220 200 75	300		$I_{C}$ =-10mA, $V_{CE}$ =-2 $V^{(a)}$ $I_{C}$ =-1A, $V_{CE}$ =-2 $V^{(a)}$ $I_{C}$ =-3A, $V_{CE}$ =-2 $V$
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>		-20 -60 -135 -180	-30 -80 -180 -250	mV mV mV mV	$I_{C}=-100\text{mA}, I_{B}=-10\text{mA}^{(a)}$ $I_{C}=-1\text{A}, I_{B}=-100\text{mA}^{(a)}$ $I_{C}=-3\text{A}, I_{B}=-300\text{mA}^{(a)}$ $I_{C}=-4\text{A}, I_{B}=-400\text{mA}^{(a)}$
Base-emitter saturation voltage	V <sub>BE(sat)</sub>		-0.90	-1.00	V	I <sub>C</sub> =-3A, I <sub>B</sub> =-300mA <sup>(a)</sup>
Base-emitter turn-on voltage	V <sub>BE(on)</sub>		-0.81	-0.90	V	I <sub>C</sub> =-3A, V <sub>CE</sub> =-2V <sup>(a)</sup>
Transition frequency	f <sub>T</sub>		150		MHz	lc=-100mA, V <sub>CE</sub> =-10V, f=50MHz
Output capacitance	C <sub>obo</sub>		39		pF	V <sub>CB</sub> =-10V, f=1MHz
Delay timetime	t <sub>(d)</sub>		21		ns	V <sub>CC</sub> =-10V, I <sub>C</sub> =-1A,
Rise time	t <sub>(r)</sub>		12		ns	I <sub>B1</sub> =I <sub>B2</sub> =-100mA
Storage time	t <sub>(stg)</sub>		410		ns	
Fall time	t <sub>(f)</sub>		35		ns	

## Electrical characteristics (at $T_{amb}$ = 25°C unless otherwise stated)

### NOTES:

(a) Measured under pulsed conditions. Pulse width= $300\mu$ S. Duty cycle  $\leq 2\%$ .

## **Typical characteristics**

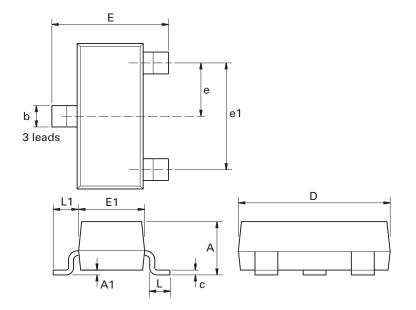


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## Package outline - SOT23



Dim.	Millin	neters	Inches		Dim.	Millin	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.	
А	-	1.12	-	0.044	e1	1.90	NOM	0.075	NOM	
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104	
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055	
С	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236	
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024	
е	0.95	NOM	0.037	NOM	-	-	-	-	-	

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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